

# 产品规格书

批准	审核	校核	编制
纪春华	朴致均	赵宇辉	郑羿
2019.08.05	2019.08.05	2019.08.05	2019.08.05

## 规格书更改履历:

序号	更改内容	履历号	更改时间	责任人
1	新规制定	000	2019.08.05	郑羿

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## SWITCHING REGULATOR APPLICATIONS

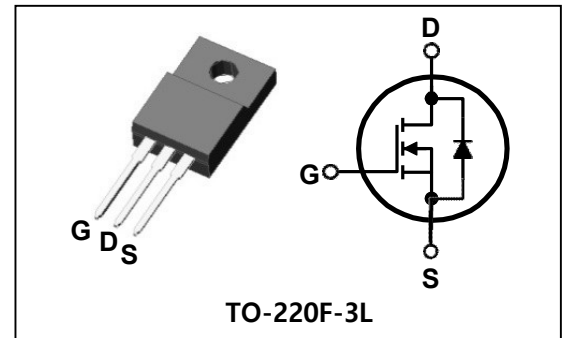
### Features

- High Voltage :  $BV_{DSS}=650V$ (Min.)
- Low  $C_{rss}$  :  $C_{rss}=14.5pF$ (Typ.)
- Low gate charge :  $Q_g=38nC$ (Typ.)
- Low  $R_{DS(on)}$  :  $R_{DS(on)}=0.88\Omega$ (Max.)

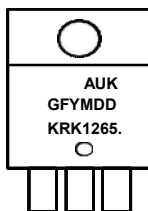
### Ordering Information

Type No.	Marking	Package Code
KRK1265F	KRK1265.	TO-220F-3L
KRK1265FA	KRK1265.	TO-220F-3L

### PIN Connection



### Marking Diagram



Column 1 : Manufacturer

Column 2 : Production Information  
e.g.) GFYMDD

- . G : Option Code (H : Halogen Free)

- . F : Factory management code

- . YMDD : Date Code (year, month, date)

Column 3 : Device Code . Dalian

### Absolute maximum ratings ( $T_C=25^\circ C$ unless otherwise noted)

Characteristic	Symbol	Rating	Unit	
Drain-source voltage	$V_{DSS}$	650	V	
Gate-source voltage	$V_{GSS}$	$\pm 30$	V	
Drain current (DC) *	$I_D$	$T_C=25^\circ C$	12	A
		$T_C=100^\circ C$	7.58	A
Drain current (Pulsed) *	$I_{DM}$	48	A	
Power dissipation	$P_D$	32	W	
Avalanche current (Single) ②	$I_{AS}$	12	A	
Single pulsed avalanche energy ②	$E_{AS}$	140	mJ	
Avalanche current (Repetitive) ①	$I_{AR}$	12	A	
Repetitive avalanche energy ①	$E_{AR}$	3.2	mJ	
Junction temperature	$T_J$	150	$^\circ C$	
Storage temperature range	$T_{stg}$	-55~150		

\* Limited by maximum junction temperature

Characteristic	Symbol	Typ.	Max.	Unit	
Thermal resistance	Junction-case	$R_{th(J-C)}$	-	3.9	$^\circ C/W$
	Junction-ambient	$R_{th(J-A)}$	-	62.5	

## Electrical Characteristics (T<sub>C</sub>=25°C unless otherwise noted)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit	
Drain-source breakdown voltage	BV <sub>DSS</sub>	I <sub>D</sub> =250μA, V <sub>GS</sub> =0V	650	-	-	V	
Gate threshold voltage	V <sub>GS(th)</sub>	I <sub>D</sub> =250μA, V <sub>DS</sub> =V <sub>GS</sub>	2.0	-	5.0	V	
Drain-source cut-off current	I <sub>DSS</sub>	V <sub>DS</sub> =650V, V <sub>GS</sub> =0V	-	-	1	μA	
Gate leakage current	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =±30V	-	-	±100	nA	
Drain-source on-resistance ④	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =6.0A	-	0.68	0.88	Ω	
Forward transfer conductance ④	g <sub>fs</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =6.0A	-	13.5	-	S	
Input capacitance	C <sub>iss</sub>	V <sub>GS</sub> =0V, V <sub>DS</sub> =25V f=1 MHz	-	2470	-	pF	
Output capacitance	C <sub>oss</sub>		-	160	-		
Reverse transfer capacitance	C <sub>rss</sub>		-	14.5	-		
Turn-on delay time	t <sub>d(on)</sub>	V <sub>DD</sub> =325V, I <sub>D</sub> =12A R <sub>G</sub> =25Ω	-	38	-	ns	
Rise time	t <sub>r</sub>		-	95	-		
Turn-off delay time	t <sub>d(off)</sub>		③④	-	155		-
Fall time	t <sub>f</sub>		-	105	-		
Total gate charge	Q <sub>g</sub>	V <sub>DS</sub> =520V, V <sub>GS</sub> =10V I <sub>D</sub> =12A	-	38	45	nC	
Gate-source charge	Q <sub>gs</sub>		-	15	-		
Gate-drain charge	Q <sub>gd</sub>		③④	-	9		-

## Source-Drain Diode Ratings and Characteristics (T<sub>C</sub>=25°C unless otherwise noted)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Source current (DC)	I <sub>S</sub>	Integral reverse diode in the MOSFET	-	-	12	A
Source current (Pulsed) ①	I <sub>SM</sub>		-	-	48	
Forward voltage ④	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =12A	-	-	1.4	V
Reverse recovery time	t <sub>rr</sub>	I <sub>S</sub> =12A, V <sub>GS</sub> =0V dI <sub>F</sub> /dt=100A/μs	-	500	-	ns
Reverse recovery charge	Q <sub>rr</sub>		-	4.3	-	μC

Note ;

- ① Repetitive rating : Pulse width limited by maximum junction temperature
- ② L=1.8mH, I<sub>AS</sub>=12A, V<sub>DD</sub>=50V, R<sub>G</sub>=25Ω, Starting T<sub>J</sub>=25°C
- ③ Pulse Test : Pulse width≤300μs, Duty cycle≤2%
- ④ Essentially independent of operating temperature

## Electrical Characteristic Curves

Fig. 1 Typical Output Characteristics

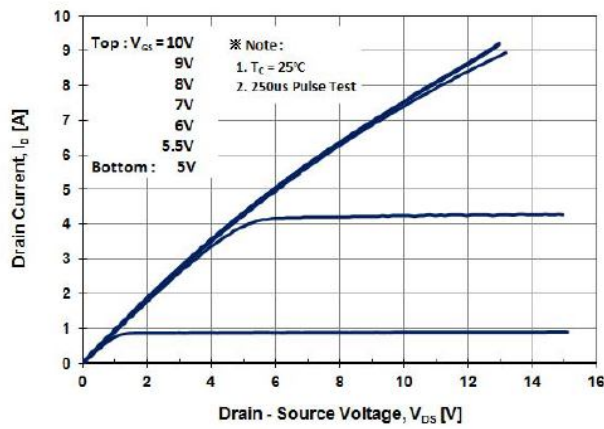


Fig. 2 Typical Output Characteristics

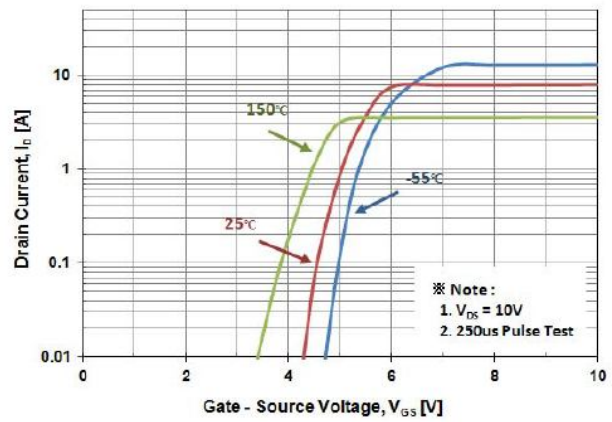


Fig.3 On-Resistance Variation with Drain Current and Gate Voltage

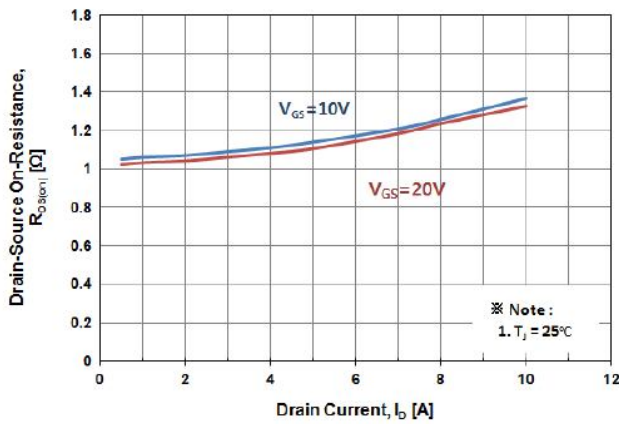


Fig. 4 Body Diode Forward Voltage Variation with Source Current

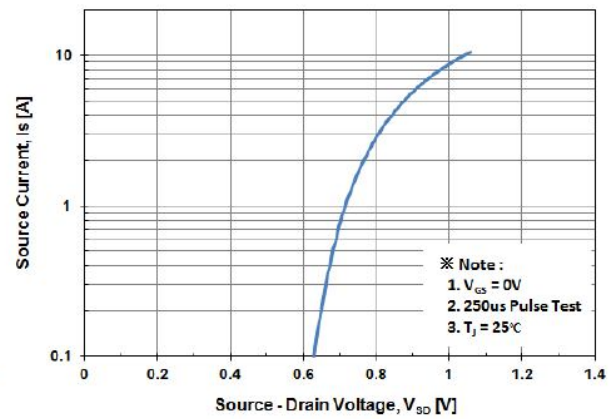


Fig. 5 Typical Capacitance Characteristics

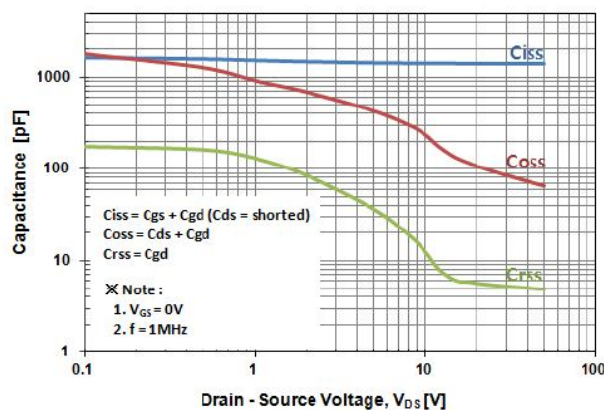
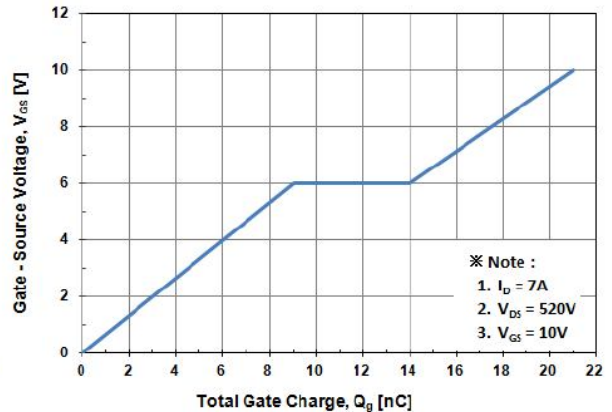


Fig. 6 Typical Total Gate Charge Characteristics



## Electrical Characteristic Curves

Fig. 7 Breakdown Voltage Variation vs. Temperature

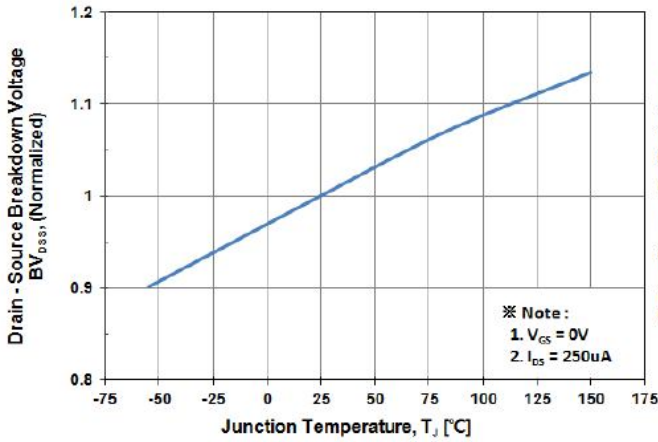


Fig. 8 On-Resistance Variation vs. Temperature

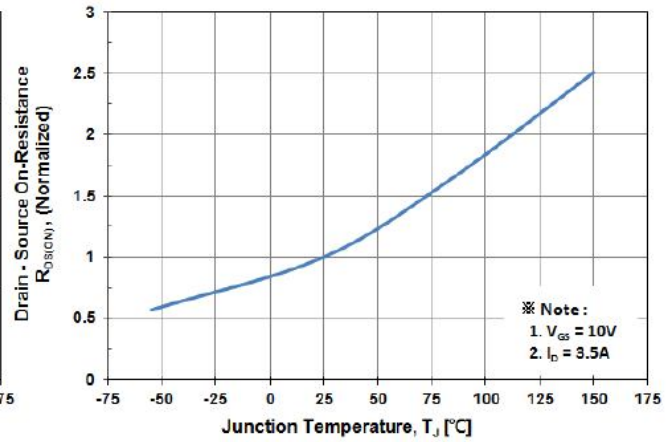


Fig. 9 Maximum Drain Current vs. Case Temperature

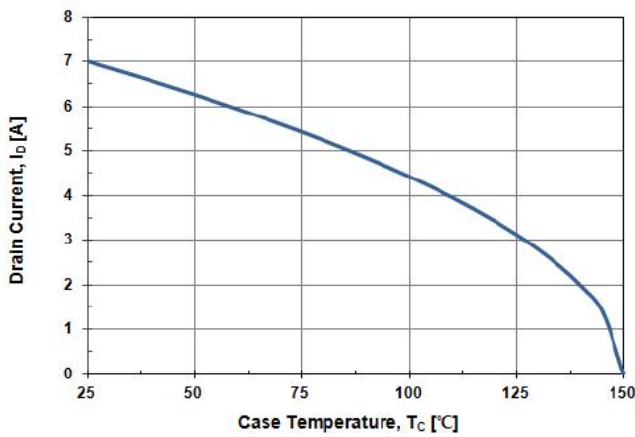


Fig. 10 Maximum Safe Operating Area

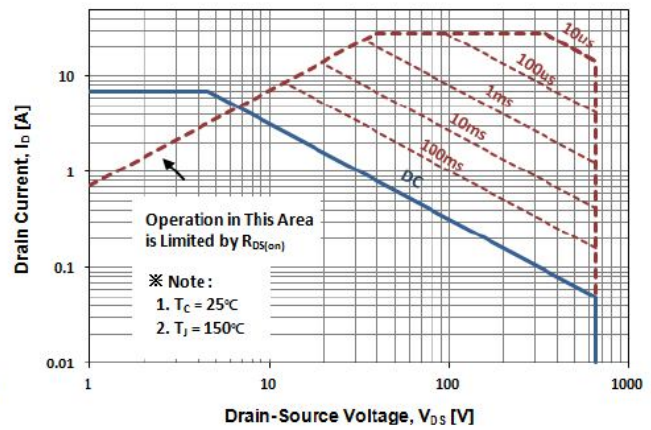
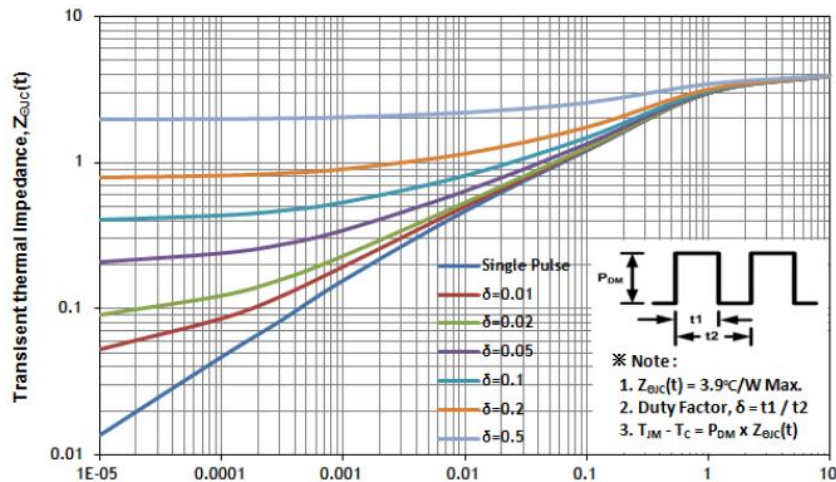
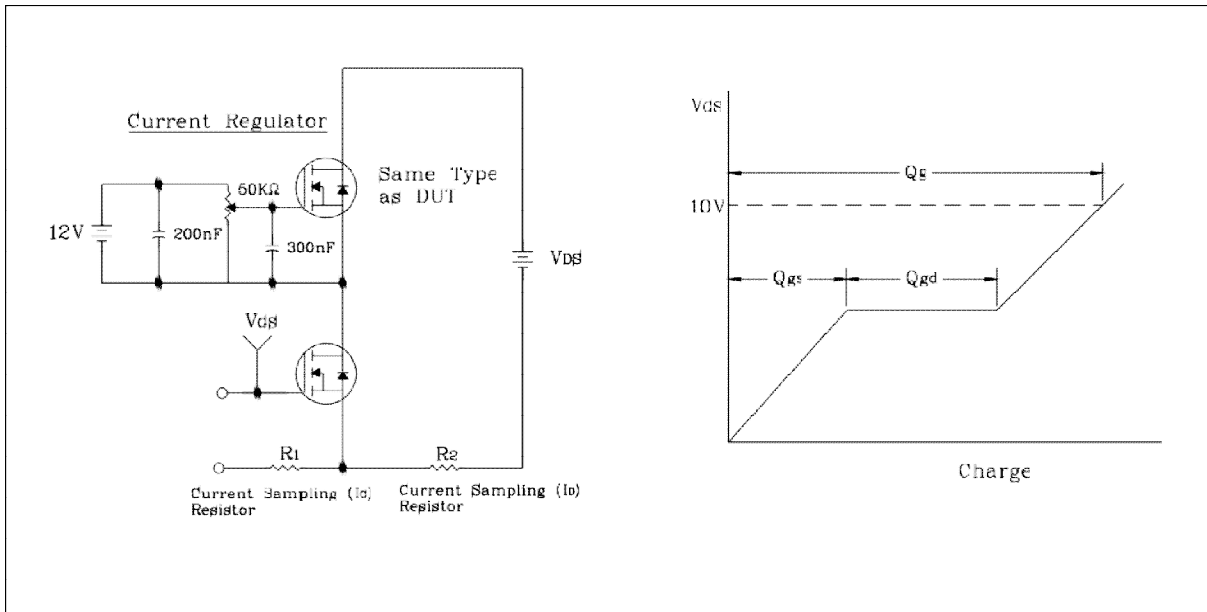


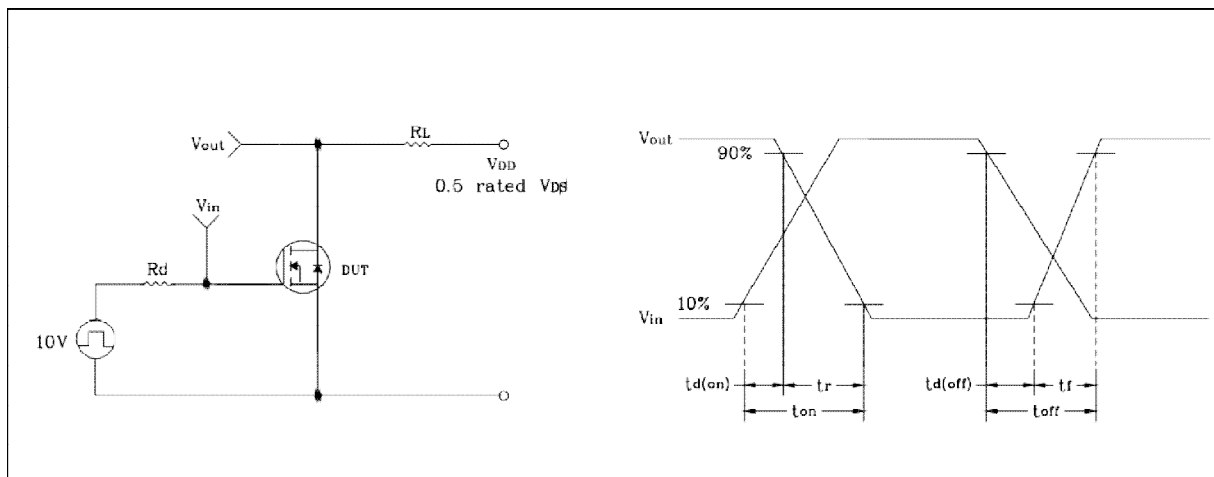
Fig. 11 Transient Thermal Impedance



**Fig. 12 Gate Charge Test Circuit & Waveform**



**Fig. 13 Resistive Switching Test Circuit & Waveform**



**Fig. 14  $E_{AS}$  Test Circuit & Waveform**

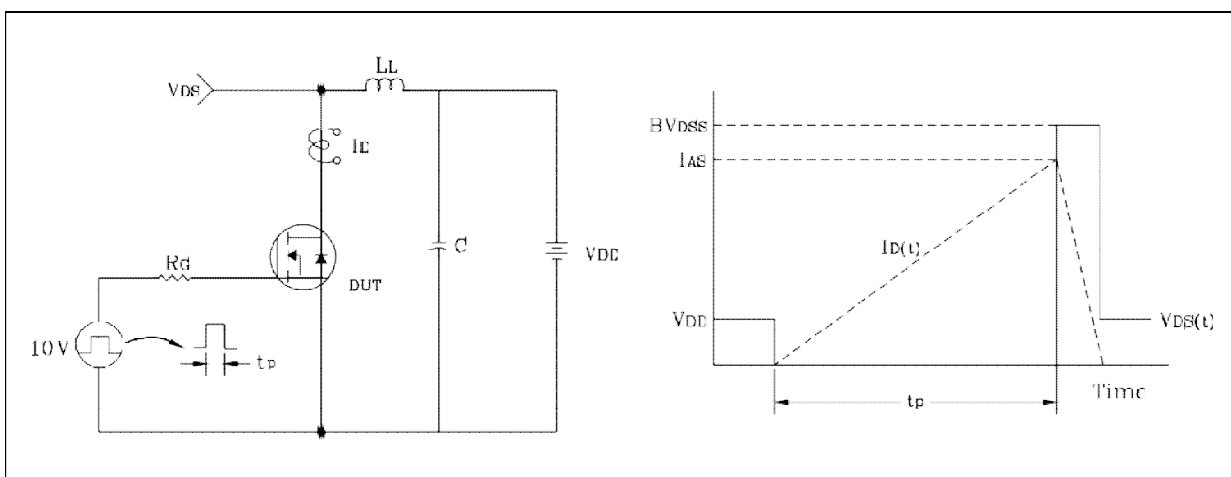
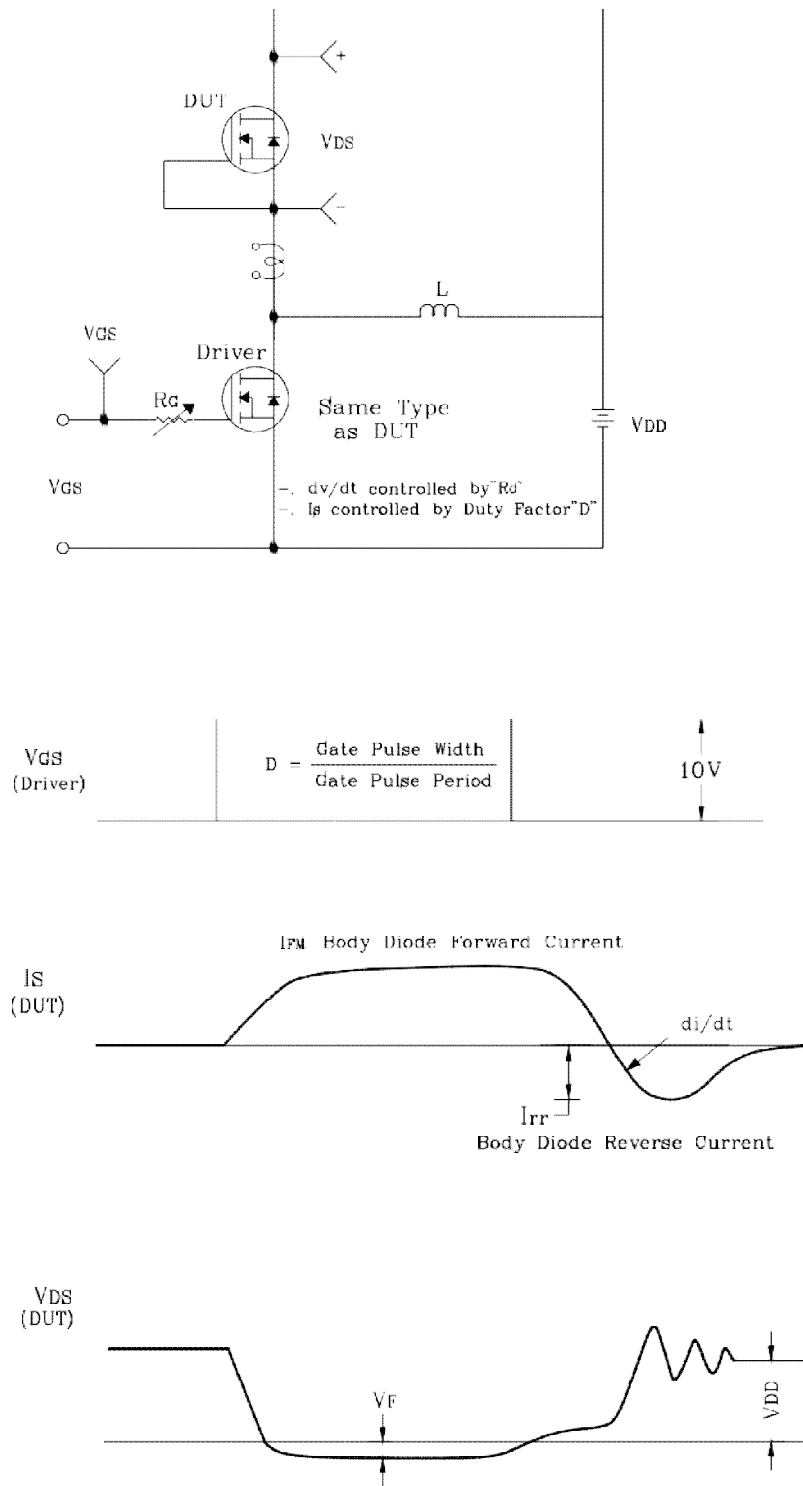


Fig. 15 Diode Reverse Recovery Time Test Circuit & Waveform

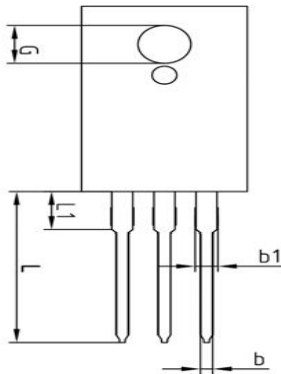
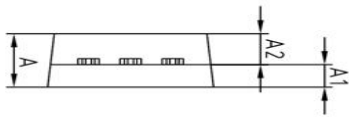
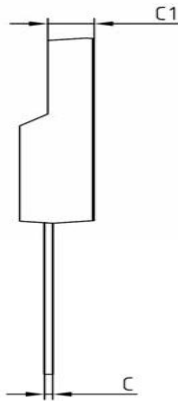
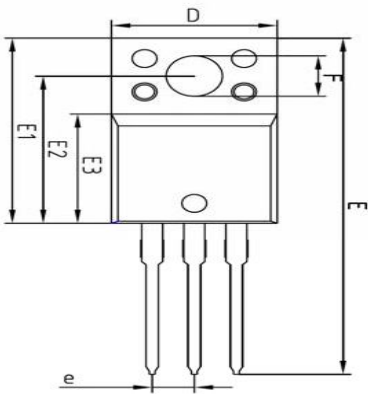




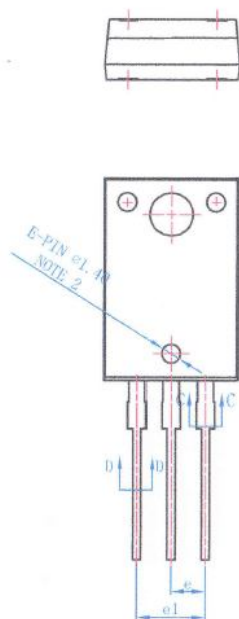
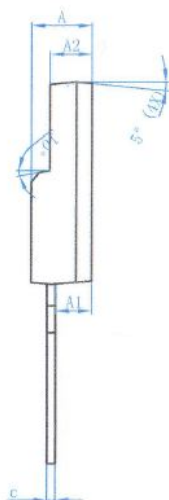
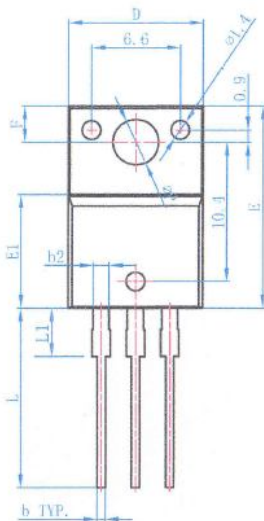
# KRK1265F/FA

## Outline Dimension

unit: mm



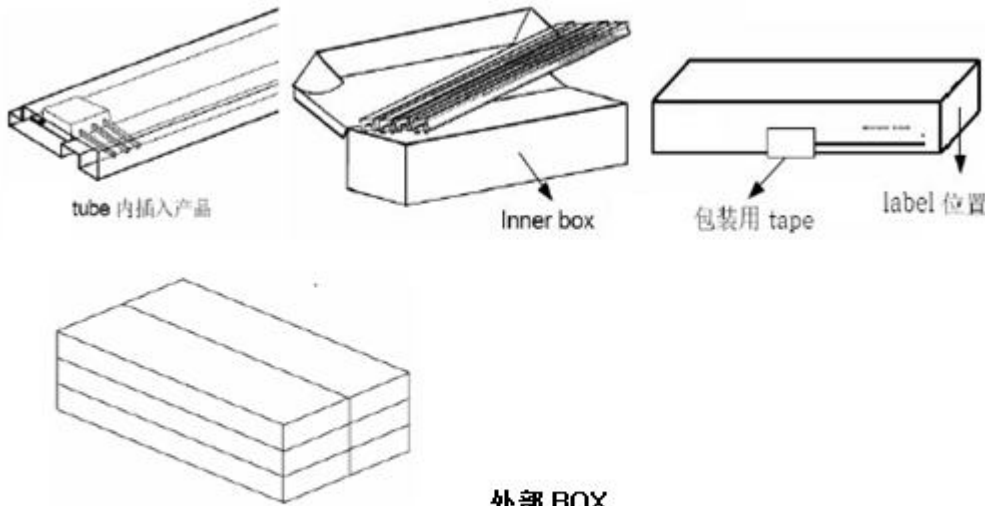
SYMBOL	MILLIMETERS			NOTE
	MINIMUM	NOMINAL	MAXIMUM	
A	-	-	4.60	
A1	2.45	2.50	2.55	
A2	1.95	2.00	2.05	
b	0.65	0.75	0.85	
b1	1.07	1.27	1.47	
C	0.40	0.50	0.60	
C1	2.70	2.80	2.90	
D	9.90	10.00	10.10	
E	28.00	-	28.60	
E1	15.50	15.60	15.70	
E2	12.30	12.40	12.50	
E3	9.15	9.20	9.25	
F	3.30	3.40	3.50	
G	3.10	3.20	3.30	
e	2.54 BSC			
L	12.40	-	13.00	
L1	3.46 BSC			



SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	4.20	4.50	4.80	0.165	0.177	0.189
A1	2.50	—	2.90	0.098	—	0.114
A2	2.90	3.10	3.30	0.114	0.122	0.130
b	0.30	0.60	0.90	0.012	0.024	0.035
b1	0.30	—	0.90	0.012	—	0.035
b2	1.00	1.20	1.40	0.039	0.047	0.055
b3	1.00	—	1.40	0.039	—	0.055
c	—	0.60	—	—	0.024	—
D	9.90	10.00	10.10	0.390	0.394	0.398
E	14.80	15.10	15.40	0.583	0.594	0.606
E1	8.40	8.50	8.60	0.331	0.335	0.339
e	—	2.54BSC	—	—	0.100BSC	—
e1	—	5.10BSC	—	—	0.200BSC	—
F	2.55	2.70	2.85	—	0.106	0.112
L	13.00	13.40	13.80	0.512	0.528	0.543
L1	3.45	3.60	3.75	0.136	0.142	0.148
eP	2.90	3.20	3.50	0.114	0.126	0.138



## Packing Spec



PKG	个/TUBE	TUBE/内部 BOX	个/内部 BOX	个/外部 BOX
TO220F	50	20	1,000	6,000

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